

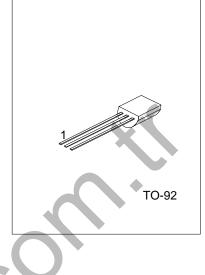
2N5088/2N5089

NPN EPITAXIAL SILICON TRANSISTOR

NPN GENERAL PURPOSE AMPLIFIER

DESCRIPTION

The devices are designed for low noise, high gain, general purpose amplifier applications at collector currents from $1\mu A\sim 50 mA.$



ORDERING INFORMATION

Order	Dookogo	Pin Assignment			Dealving		
Lead Free	Halogen Free	Package	1	2	3	Packing	
2N5088L-T92-B	2N5088G-T92-B	TO-92	E	В	С	Tape Box	
2N5088L-T92-K	2N5088G-T92-K	TO-92	Е	В	С	Bulk	
2N5088L-T92-R	2N5088G-T92-R	TO-92	Е	В	С	Tape Reel	
2N5089L-T92-B	2N5089G-T92-B	TO-92	Е	В	С	Tape Box	
2N5089L-T92-K	2N5089G-T92-K	TO-92	Е	В	С	Bulk	
2N5089L-T92-R	2N5089G-T92-R	TO-92	Е	В	С	Tape Reel	

Note: Pin Assignment: E: Emitter B: Base C: Collector

2N5088 <u>L</u> - <u>T92</u> - <u>B</u>	
(1)Packing Type	(1) B: Tape Box, K: Bulk, R: Tape Reel
(2)Package Type	(2) T92: TO-92
(3)Lead Free	(3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter voltage	2N5088	N	30	N/	
	2N5089	V _{CEO}	25	- V	
Collector-Base voltage	2N5088	N/	35	V	
	2N5089	V _{CBO}	30	v	
Emitter-Base Voltage		V _{EBO}	4.5	V	
Collector Current-Continuous		lc	100	mA	
Power Dissipation			625	mW	
Derate Above 25°C		PD	5	mW/°C	
Junction Temperature		TJ	150	°C	
Storage Temperature		T _{STG}	-55 ~ +150	°C	

Note 1. These ratings are based on a maximum junction temperature of 150 degrees C.

2. These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

3. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **THERMAL DATA** (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	200	°C/W
Junction to Case	θJC	83.3	°C/W

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS								
Collector-Emitter Breakdown Voltage	2N5088 2N5089	V(BR)CEO	I _C =1.0mA, I _B =0 (Note)		30 25			V
Collector-Base Breakdown Voltage	2N5088 2N5089	V _{(BR)CBO}	I _C =100μΑ, I _E =0		35 30			V
Collector Cut-Off Current	2N5088 2N5089	Ісво	V _{CB} =20V, I _E =0 V _{CB} =15V, I _E =0				50 50	nA
Emitter Cutoff Current		I _{EBO}	V _{EB} =3.0V, I _C =0 V _{EB} =4.5V, I _C =0				50 100	nA
DC Current Gain		h _{FE}	V _{CE} =5.0V, I _C =100μA	2N5088 2N5089	300 400		900 1200	
			V _{CE} =5.0V, I _C =1.0mA	2N5088 2N5089	350 450			
			V _{CE} =5.0V, I _C =10mA (Note)	2N5088 2N5089	300 400			
Collector-Emitter Saturation Voltage		V _{CE(SAT)}	I _C =10mA, I _B =1.0mA				0.5	V
Base-Emitter On Voltage		V _{BE(ON)}	I _C =10mA, V _{CE} =5.0V				0.8	V
SMALL SIGNAL CHARACT	ERISTICS	-				-	-	
Current Gain-Bandwidth Product		f⊤	V _{CE} =5.0mA, I _C =500μA, f=20MHz		50			MHz
Collector-Base Capacitance		C _{CB}	V _{CB} =5.0V, I _E =0, f=100kHz				4	pF
Emitter-Base Capacitance		CEB	V _{EB} =0.5V, I _C =0, f=100kHz				10	pF
Small-Signal Current Gain	2N5088 2N5089	h _{FE}	V _{CE} =5.0V, I _C =1.0mA, f=1.0kHz		350 450		1400 1800	
Noise Figure	2N5088 2N5089	NF	V _{CE} =5.0V, I _C =100μA, R _S =10kΩ, f=10KHz ~ 15.7kHz				3.0 2.0	dB

Note Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%



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